

ABSTRACT OF THE DISCLOSURE

An EUV photomask having a main area and a scribe lane area and reflecting EUV light includes a reflective multilayer film and an absorption pattern, wherein the scribe lane area includes first and second lanes, wherein the first lane includes first and second sub-lanes extending in the same direction as an extending direction of the first lane, wherein the first sub-lane includes a first dummy pattern that is a portion of the absorption pattern, and the second sub-lane includes a second dummy pattern that is a portion of the absorption pattern, and when EUV light that is not absorbed by the first and second dummy patterns and is reflected by the reflective multilayer film is irradiated at least twice by overlapping a negative tone photoresist, an amount of light exceeds a threshold dose of light in the negative tone photoresist corresponding to the first lane.

FIG. 3